



SE12Q10BDD3H

ESD Protection Diode

FEATURES

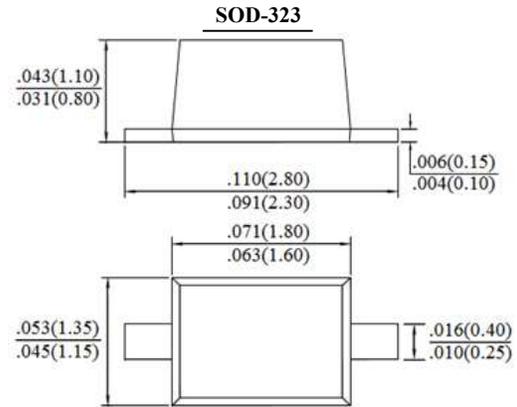
- 350W Peak Pulse Power per Line (tp=8/20μs)
- IEC61000-4-2(ESD) 30kV(Air), 30kV(Contact)
- Protect One Power or I/O Port
- Low Clamping Voltage
- Low Leakage current
- Bi-directional Configurations
- Suffix " H " indicated Halogen-free part, ex.SE12Q10BDD3H

APPLICATIONS

- Notebooks, Desktops & Servers
- Communication system
- Cellular handsets and accessories

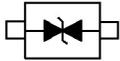
MECHANICAL DATA

Case : SOD-323



Dimensions in inches and (millimeters)

PIN CONFIGURATION



Maximum Ratings (Rating at 25°C ambient temperature unless otherwise specified)

Parameter	Symbol	Value	Units
Peak Pulse Power (tp=8/20μs waveform)	P _{PP}	350	W
ESD per IEC 61000-4-2 (Air)	V _{ESD}	±30	kV
ESD per IEC 61000-4-2 (Contact)		±30	
Operating Junction Temperature	T _J	-55 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C



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Electrical Characteristics (Rating at 25°C ambient temperature unless otherwise specified)

Parameter	Symbol	Min	Typ.	Max	Units
Reverse Stand-Off Voltage	V_{RWM}	-	-	12	V
Reverse Breakdown Voltage	$I_R = 1\text{mA}$ $V_{(BR)}$	13.3	-	-	V
Reverse Leakage Current	$V_R = 12\text{V}$ I_R	-	-	1	μA
Clamping Voltage	$I_{PP} = 5\text{A}$, $t_p = 8/20\mu\text{s}$	-	-	19	V
	$I_{PP} = 15\text{A}$, $t_p = 8/20\mu\text{s}$	-	-	25	
Junction Capacitance	$V_R=0\text{V}$, $f=1\text{MHz}$ C_J	-	-	100	pF

RATINGS AND CHARACTERISTIC CURVES

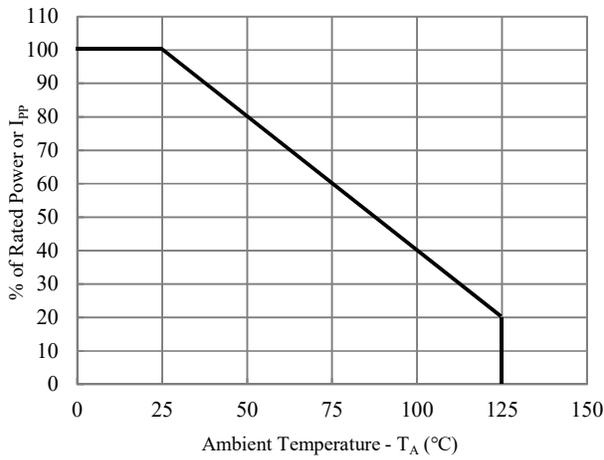


Fig.1-Power Derating Curve

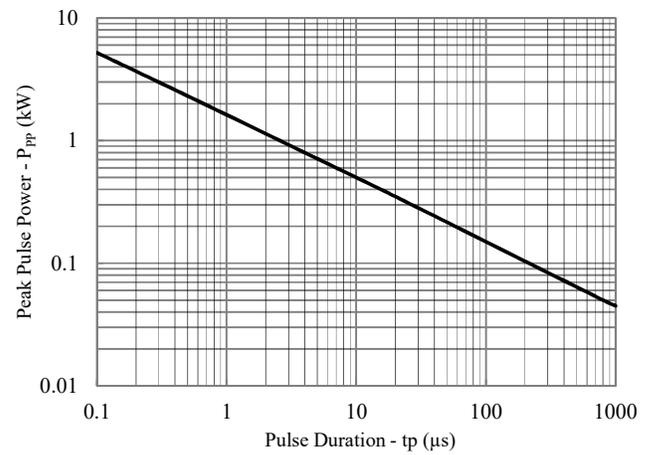


Fig.2-Non-Repetitive Peak Pulse Power vs. Pulse Time

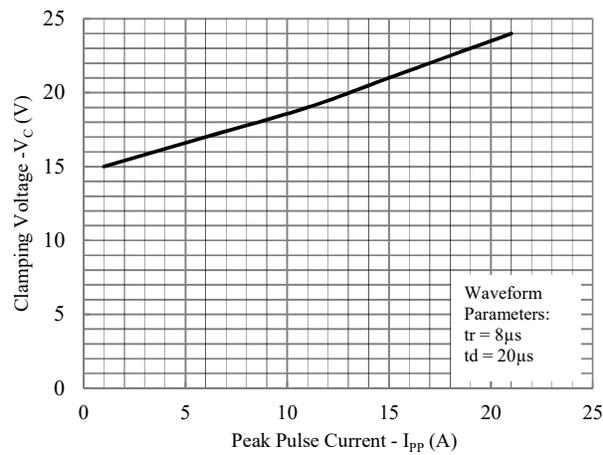


Fig.3-Clamping Voltage vs. Peak Pulse Current